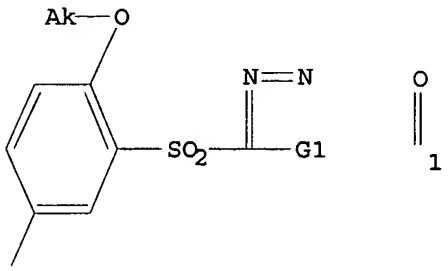
```
=> d his

     (FILE 'HOME' ENTERED AT 13:22:05 ON 14 NOV 2005)

     FILE 'REGISTRY' ENTERED AT 13:22:13 ON 14 NOV 2005
L1             STRUCTURE UPLOADED
L2           1 S L1
L3           5 S L1 FULL

     FILE 'CAPLUS' ENTERED AT 13:23:07 ON 14 NOV 2005
L4           1 S L3

=> d que l4 stat
L1             STR
```




```
G1 SO2, [@1]


Structure attributes must be viewed using STN Express query preparation.
L3           5 SEA FILE=REGISTRY SSS FUL L1
L4           1 SEA FILE=CAPLUS ABB=ON  PLU=ON  L3


=> d ibib iabs hitstr
```

L4 ANSWER 1 OF 1 CAPLUS COPYRIGHT 2005 ACS on STN
ACCESSION NUMBER: 2004:701845 CAPLUS
DOCUMENT NUMBER: 141:233204
TITLE: Novel sulfonyldiazomethanes, photoacid generators, resist compositions, and patterning process
INVENTOR(S): Ohsawa, Youichi; Kobayashi, Katsuhiro; Yanagi, Yoshitaka; Maeda, Kazunori
PATENT ASSIGNEE(S): Japan
SOURCE: U.S. Pat. Appl. Publ., 41 pp.
CODEN: USXXCO
DOCUMENT TYPE: Patent
LANGUAGE: English
FAMILY ACC. NUM. COUNT: 1
PATENT INFORMATION:

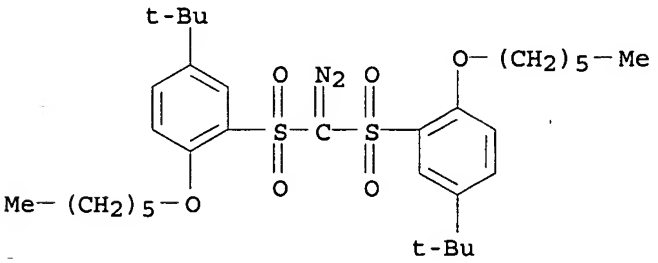
PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 2004167322	A1	20040826	US 2004-776159	20040212
JP 2004244360	A2	20040902	JP 2003-35077	20030213

PRIORITY APPLN. INFO.: JP 2003-35077 A 20030213
OTHER SOURCE(S): MARPAT 141:233204

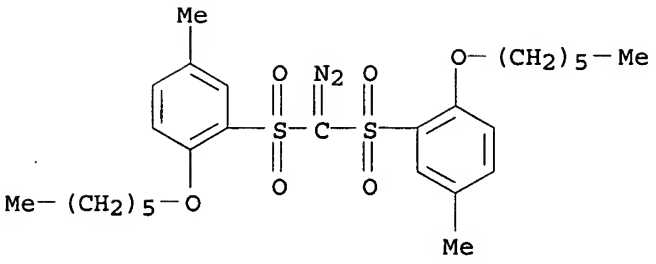
ABSTRACT:
A chemical amplification type resist composition comprising a specific benzenesulfonyldiazomethane containing a long-chain alkoxyl group at the 2-position on benzene ring has many advantages including improved resolution, improved focus latitude, minimized line width variation or shape degradation even on long-term PED, minimized debris left after coating, development and peeling, and improved pattern profile after development and is thus suited for microfabrication.

IT **746652-33-5P 746652-37-9P 746652-38-0P**
746652-39-1P 746652-40-4P
RL: CAT (Catalyst use); PRP (Properties); SPN (Synthetic preparation); PREP (Preparation); USES (Uses)
(sulfonyldiazomethane photoacid for resist compns.)

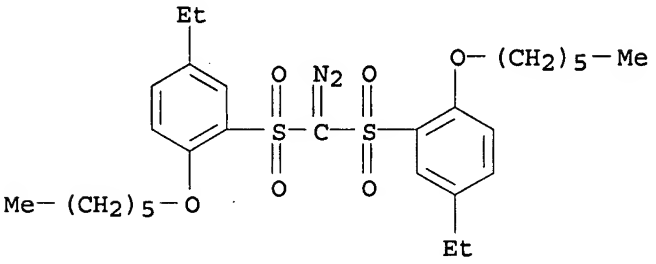
RN 746652-33-5 CAPLUS
CN Benzene, 1,1'-[(diazomethylene)disulfonyl]bis[5-(1,1-dimethylethyl)-2-(hexyloxy)- (9CI) (CA INDEX NAME)



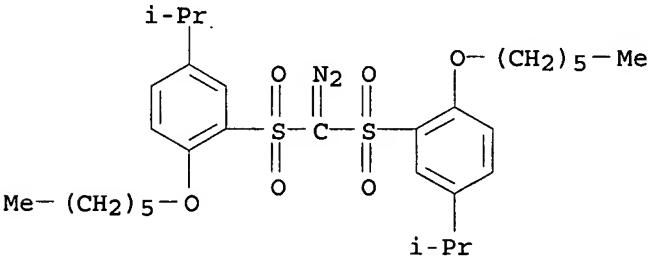
RN 746652-37-9 CAPLUS
CN Benzene, 1,1'-[(diazomethylene)disulfonyl]bis[2-(hexyloxy)-5-methyl- (9CI) (CA INDEX NAME)



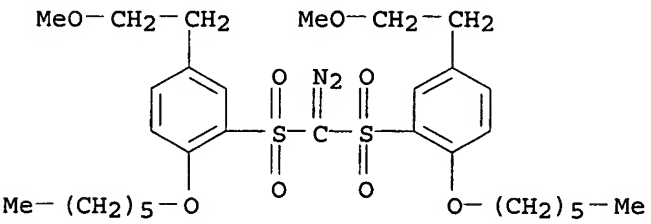
RN 746652-38-0 CAPLUS
CN Benzene, 1,1'-[(diazomethylene)disulfonyl]bis[5-ethyl-2-(hexyloxy)- (9CI) (CA INDEX NAME)



RN 746652-39-1 CAPLUS
CN Benzene, 1,1'-[(diazomethylene)disulfonyl]bis[2-(hexyloxy)-5-(1-methylethyl)- (9CI) (CA INDEX NAME)



RN 746652-40-4 CAPLUS
CN Benzene, 1,1'-[(diazomethylene)disulfonyl]bis[2-(hexyloxy)-5-(2-methoxyethyl)- (9CI) (CA INDEX NAME)



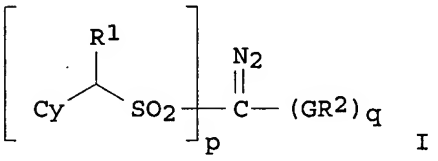
```
=> => d que l10 stat
L5            19 SEA FILE=CAPLUS ABB=ON  PLU=ON  "OHSAWA YOUICHI"/AU
L6            55 SEA FILE=CAPLUS ABB=ON  PLU=ON  "KOBAYASHI KATSUHIRO"/AU
L7             8 SEA FILE=CAPLUS ABB=ON  PLU=ON  "YANAGI YOSHITAKA"/AU
L8            52 SEA FILE=CAPLUS ABB=ON  PLU=ON  "MAEDA KAZUNORI"/AU
L9           118 SEA FILE=CAPLUS ABB=ON  PLU=ON  L5 OR L6 OR L7 OR L8
L10           14 SEA FILE=CAPLUS ABB=ON  PLU=ON  L9 AND (?DIAZOMETHANE OR
                 DIAZOMETHANE)

=> d 1-14 bib abs
```

L10 ANSWER 1 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2005:182216 CAPLUS
DN 142:287807
TI Novel **sulfonyldiazomethane** compounds, photoacid generator, resist materials and patterning process using the same
IN **Kobayashi, Katsuhiro**; **Ohsawa, Youichi**; Kinsho, Takeshi; Fukuda, Eiji; Tanaka, Shigeo
PA Shin-Etsu Chemical Co., Ltd., Japan
SO U.S. Pat. Appl. Publ., 34 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI US 2005048395	A1	20050303	US 2004-929059	20040827
JP 2005068117	A2	20050317	JP 2003-304060	20030828
PRAI JP 2003-304060	A	20030828		

OS MARPAT 142:287807
GI



I

AB Provided are **sulfonyldiazomethane** compds. and photoacid generators suited for resist materials which generate less foreign matters after application, development and peeling, and in particular, are excellent in the pattern profile after the development; and resist materials and patterning process using them. Provided are **sulfonyldiazomethane** compds. represented by formula I(R1 = H, C1-6 alkyl; Cy = cyclohexyl, C1-6 alkyl, C1-6 alkoxy; R2 = C1-10 alkyl, C6-14 aryl; p = 1, 2; q = 0, 1; p+q=2). Also provides are photoacid generators containing the **sulfonyldiazomethane** compds., and a chemical amplification resist material comprising (A) a resin which changes its solubility in an alkali developer by action of an acid, and (B) a **sulfonyldiazomethane** compound of formula I capable of generating an acid by exposure to radiation. Provided is a patterning process comprising steps of applying the above-described resist material onto a substrate to form a coating process, heating the coating process, exposing the coating process, and developing the exposed coating process in a developer after an optional heat treatment.

L10 ANSWER 2 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:701845 CAPLUS
DN 141:233204
TI Novel sulfonyldiazomethanes, photoacid generators, resist compositions, and patterning process
IN **Ohsawa, Youichi; Kobayashi, Katsuhiro; Yanagi, Yoshitaka; Maeda, Kazunori**
PA Japan
SO U.S. Pat. Appl. Publ., 41 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004167322	A1	20040826	US 2004-776159	20040212
	JP 2004244360	A2	20040902	JP 2003-35077	20030213
PRAI	JP 2003-35077	A	20030213		

OS MARPAT 141:233204
AB A chemical amplification type resist composition comprising a specific **benzenesulfonyldiazomethane** containing a long-chain alkoxyl group at the 2-position on benzene ring has many advantages including improved resolution, improved focus latitude, minimized line width variation or shape degradation even on long-term PED, minimized debris left after coating, development and peeling, and improved pattern profile after development and is thus suited for microfabrication.

L10 ANSWER 3 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:701689 CAPLUS
DN 141:233196
TI Sulfonyldiazomethanes for photoacid generators and resist patterning process
IN **Ohsawa, Youichi; Kobayashi, Katsuhiro; Yanagi, Yoshitaka; Maeda, Kazunori**
PA Japan
SO U.S. Pat. Appl. Publ., 38 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004166432	A1	20040826	US 2004-776291	20040212
	JP 2004244358	A2	20040902	JP 2003-35055	20030213
PRAI	JP 2003-35055	A	20030213		

OS MARPAT 141:233196
AB A chemical amplification type resist composition comprising a specific **sulfonyldiazomethane** containing long-chain alkoxyl groups has many advantages including improved resolution, improved focus latitude, minimized line width variation or shape degradation even on long-term PED, minimized debris left after coating, development and peeling, and improved pattern profile after development and is thus suited for microfabrication.

L10 ANSWER 4 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:142669 CAPLUS
DN 140:207466
TI Photoacid generators, chemically amplified positive resist compositions, and patterning process
IN **Maeda, Kazunori**; **Ohsawa, Youichi**; Watanabe, Satoshi
PA Japan
SO U.S. Pat. Appl. Publ., 30 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004033440	A1	20040219	US 2003-636654	20030808
	JP 2004133393	A2	20040430	JP 2003-205698	20030804
PRAI	JP 2002-233510	A	20020809		

OS MARPAT 140:207466
AB Photoacid generators capable of generating 2,4,6-triisopropylbenzenesulfonic acid upon exposure to actinic radiation are suited for use in chemical amplified pos. resist compns. Due to the low diffusion of 2,4,6-triisopropylbenzenesulfonic acid, the compns. have many advantages including improved resolution, improved focus latitude, and minimized line width variation or shape degradation even on long-term PED.

L10 ANSWER 5 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:142668 CAPLUS
DN 140:207465
TI Novel sulfonydiazomethanes, photoacid generators, resist compositions, and patterning process
IN **Ohsawa, Youichi**; Watanabe, Satoshi; **Maeda, Kazunori**
PA Japan
SO U.S. Pat. Appl. Publ., 31 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2004033432	A1	20040219	US 2003-636541	20030808
	JP 2004075542	A2	20040311	JP 2002-233523	20020809
PRAI	JP 2002-233523	A	20020809		

OS MARPAT 140:207465
AB **Sulfonyldiazomethane** compds. containing a long-chain alkyl- or alkoxy-naphthyl group are novel and useful as photoacid generators. Chemical amplification type resist compns. comprising the same are suited for microfabrication because of many advantages including improved resolution, improved focus latitude, and minimized line width variation or shape degradation even on long-term PED.

L10 ANSWER 6 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2004:20123 CAPLUS
DN 140:102018
TI Photoacid generators for chemically amplified resists and their use in resists and pattern formation
IN Osawa, Yoichi; **Kobayashi, Katsuhiro**; Takemura, Katsuya; Tsuchiya, Junji; Maeda, Kazuki
PA Shin-Etsu Chemical Industry Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 76 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2004004551	A2	20040108	JP 2003-27861	20030205
PRAI	JP 2002-80566	A	20020322		

OS MARPAT 140:102018
GI

* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY - AVAILABLE VIA OFFLINE PRINT *

AB The photoacid generators are represented by I, pC(EWG):NOSO2C6H4-rR'rOn(CH2)mMe, q[C(EWG):NOSO2C6H4-rR'rOn(CH2)mMe]2, or II [R' = H, F, C1-4 alkyl, alkoxy; R = Cl, R'; n = 0, 1; m =3-11; r = 0-4; EWG = cyano, nitro, C1-3 perfluoroalkyl; p = C1-10 alkyl, C6-12 aryl; q = C1-10 alkylene, C6-18 arylene; G', G'' = S, CH:CH; G' and G'' are not S at the same time; G = H, p; two G may form ring]. Alternatively, the photoacid generators are O-arylsulfonyloximes and generate long-chain alkylbenzenesulfonic acids or alkoxybenzenesulfonic acids of HO3SC6H4-rR'rOn(CH2)mMe (R', n, m, and r are same as above) under irradiation with UV, far-UV, electron beam, x-ray, excimer laser, γ-ray, or synchrotron radiation. The claimed chemical amplified (pos.) resists contain the above photoacid generators and resins changing solubility to alkali development solns. by acids. Patterns are formed by applying the resists on substrates, heating, exposing through photomasks by ≤300 nm-wavelength high-energy beams or electron beams, optionally heating, and developing with solns.

L10 ANSWER 7 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2003:950589 CAPLUS
DN 140:21274
TI Novel sulfonyldiazomethanes, photoacid generators, resist compositions, and patterning process
IN **Kobayashi, Katsuhiro**; **Ohsawa, Youichi**; Hasegawa, Koji; Yoshihara, Takao; **Maeda, Kazunori**; Fujii, Toshihiko
PA Shin-Etsu Chemical Co., Ltd., Japan
SO U.S. Pat. Appl. Publ., 35 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

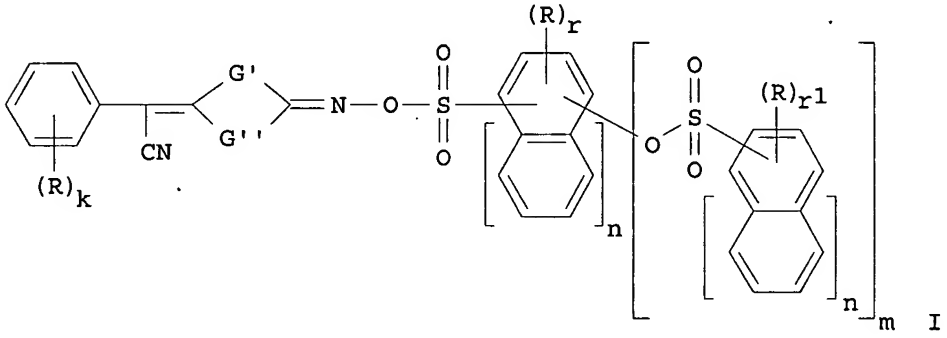
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2003224298	A1	20031204	US 2003-426623	20030501
	US 6713612	B2	20040330		
	JP 2004026809	A2	20040129	JP 2003-118155	20030423
PRAI	JP 2002-129681	A	20020501		

OS MARPAT 140:21274
AB **Sulfonyldiazomethane** compds. containing a long-chain alkylcyclohexyl group are novel and useful as photoacid generators. Chemical amplification type photoresist compns. comprising the same are suited for microfabrication because of many advantages including improved resolution, improved focus latitude, minimized line width variation or shape degradation even on long-term PED, minimized debris left after coating, development and peeling, and improved pattern profile after development.

L10 ANSWER 8 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2003:912695 CAPLUS
DN 139:401547
TI Photoacid generators and chemically amplified resist compositions for patterning process
IN **Ohsawa, Youichi; Kobayashi, Katsuhiro**; Takemura, Katsuya; Tsuchiya, Junji; **Maeda, Kazunori**
PA Shin-Etsu Chemical Co., Ltd., Japan
SO U.S. Pat. Appl. Publ., 49 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI US 2003215738	A1	20031120	US 2003-393006	20030321
US 6916591	B2	20050712		
JP 2004004614	A2	20040108	JP 2003-71473	20030317
PRAI JP 2002-80649	A	20020322		

OS MARPAT 139:401547
GI

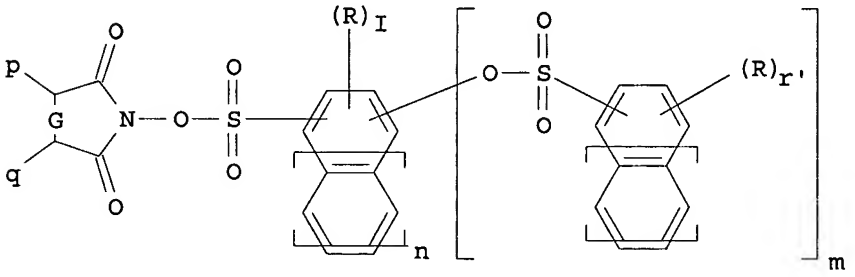


AB Photoacid generators are provided by O-arylsulfonyl-oxime compds. having general formula I (R = H, F, Cl, NO2, alkyl, alkoxy; n = 0, 1; m = 1, 2; r = 0-4; r1 = 0-5; k = 0-4; G1, G2 = S, -CH=CH-). Chemical amplified resist compns. comprising the photoacid generators have many advantages including improved resolution, improved focus latitude, minimized line width variation or shape degradation even on long-term PED, and improved pattern profile after development. Because of high resolution, the compns. are suited for microfabrication, especially by deep UV lithog.

L10 ANSWER 9 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2003:711621 CAPLUS
DN 139:252510
TI N-Solfonyloxydicarboxyimide compounds for use as photo acid-generator in chemically amplified photoresists
IN Osawa, Yoichi; **Kobayashi, Katsuhiro**; **Maeda, Kazunori**; Miyakoshi, Hiroshi; Tanaka, Yoshio
PA Shin-Etsu Chemical Industry Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 41 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI JP 2003252855	A2	20030910	JP 2002-364254	20021216
PRAI JP 2001-393194	A	20011226		

OS MARPAT 139:252510
GI



I

AB N-Solfonyloxydicarboxyimide compds. having general structure I is claimed to be used as photo acid-generator in chemical amplified photoresists (R = H, F, NO2, alkyl, alkoxy; n = 0, 1; m = 1, 2;r = 0-4, r' = 0-5; G = single or double bond; p, q = H, alkyl, or form alicyclic ring, heterocyclic ring, or aromatic ring). A chemical amplified photoresist containing the acid generator is also claimed.

L10 ANSWER 10 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2003:525404 CAPLUS
DN 139:92748
TI Novel **sulfonyldiazomethane** compounds, photoacid generators, photoresists therewith, and photolithography employing the same
IN Osawa, Yoichi; **Kobayashi, Katsuhiro**; Maeda, Kazuki
PA Shin-Etsu Chemical Industry Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 51 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2003192665	A2	20030709	JP 2002-275029	20020920
	US 2003180653	A1	20030925	US 2002-255770	20020927
	US 6689530	B2	20040210		
PRAI	JP 2001-300345	A	20010928		

OS MARPAT 139:92748
AB The compds. are [[Me(CH2)mOn]RkC6H5-n-kSO2]pC:N2(GR3)q [R = H, C1-4 alkyl(oxy); G = SO2, CO; R3 = C1-10 alkyl, C6-14 aryl; p = 1, 2; q = 0, 1; p + q = 2; n = 0, 1; m = 3-11; k = 0-4]. Photoresists containing acid-labile alkali-developable resins and radiation-sensitive acid generators including the compds. are also claimed. Further claimed is photolithog. wherein the photoresists are applied on substrates, annealed, exposed to ≤300-nm actinic rays or electron beams, (annealed,) and developed. The photoresists produce patterns containing min. number of foreign matter and having sharp profile.

L10 ANSWER 11 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2001:817219 CAPLUS
DN 135:350570
TI Chemically amplified positive resist compositions with improved resolution, pattern profile and focal latitude for deep UV lithography
IN **Ohsawa, Youichi**; Watanabe, Jun; Takeda, Takanobu; Seki, Akihiro
PA Shin-Etsu Chemical Co., Ltd., Japan
SO U.S. Pat. Appl. Publ., 33 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2001038971	A1	20011108	US 2001-799052	20010306
	US 6682869	B2	20040127		
	JP 2001324813	A2	20011122	JP 2001-57719	20010302
	TW 538312	B	20030621	TW 2001-90105205	20010306
PRAI	JP 2000-61350	A	20000307		

AB A chemical amplified, pos. resist composition is provided comprising (A) a photoacid generator and (B) a resin which changes its solubility in an alkali developer under the action of acid and has substituents of the formula: Ph-(CH2)nOCH(CH2CH3)- (n = 0,1). The composition has many advantages including improved focal latitude, improved resolution, minimized line width variation or shape degradation even on long-term PED, minimized defect left after coating, development and stripping, and improved pattern profile after development and is suited for microfabrication by any lithog., especially deep UV lithog.

L10 ANSWER 12 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2001:781404 CAPLUS
DN 135:336907
TI Chemically amplified positive resist compositions with improved resolution, pattern profile and focal latitude for deep UV lithography
IN **Ohsawa, Youichi**; Watanabe, Jun; Takeda, Takanobu; Seki, Akihiro
PA Shi-Etsu Chemical Co., Ltd., Japan
SO U.S. Pat. Appl. Publ., 34 pp.
CODEN: USXXCO
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	US 2001033994	A1	20011025	US 2001-799009	20010306
	US 6838224	B2	20050104		
	JP 2001324812	A2	20011122	JP 2001-57716	20010302
	TW 587086	B	20040511	TW 2001-90105203	20010306
PRAI	JP 2000-61357	A	20000307		

AB A chemical amplified, pos. resist composition is provided comprising (A) a photoacid generator and (B) a resin which changes its solubility in an alkali developer under the action of acid and has substituents of the formula: C6H11 -(CH2)nOCH(CH2CH3)- wherein C6H11 is cyclohexyl and n = 0,1. The composition has many advantages including improved focal latitude, improved resolution, minimized line width variation or shape degradation even on long-term PED, minimized defect left after coating, development and stripping, and improved pattern profile after development and is suited for microfabrication by any lithog., especially deep UV lithog.

RE.CNT 17 THERE ARE 17 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

L10 ANSWER 13 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2001:336588 CAPLUS
DN 134:346467
TI Resist materials containing **sulfonyldiazomethane** photoacid generators and pattern formation using them
IN **Maeda, Kazunori**; Nagata, Takashi; Watanabe, Satoshi; Osawa, Yoichi; Watanabe, Atsushi; Nakura, Shigehiro
PA Shin-Etsu Chemical Industry Co., Ltd., Japan
SO Jpn. Kokai Tokkyo Koho, 51 pp.
CODEN: JKXXAF
DT Patent
LA Japanese
FAN.CNT 1

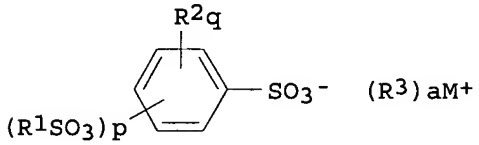
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 2001125258	A2	20010511	JP 2000-245566	20000814
	US 6338931	B1	20020115	US 2000-637595	20000815
PRAI	JP 1999-230143	A	19990816		

OS MARPAT 134:346467
AB The materials contain [(R1SO3)qR2pC6H5-p-qSO2]nC:N2(GR3)m or R1S(:O)2O-1,4-C6H4SO2C(:N2)SO2-1,4-C6H4OSO2R1 [R1, R3 = C1-10 normal, branched, or cyclic (un)substituted alkyl, C6-14 (un)substituted aryl; R2 = C1-6 normal, branched, or cyclic alkyl; G = SO2, CO; p = 0-4; q = 1-5; p + q = 1-5; n = 1, 2; m = 0, 1; n + n = 2] as photoacid generators. Patterns are formed by applying the resist materials on substrates, heating, exposing to ≤300-nm high-energy beam or electron beam through photomasks, optionally heating, and developing. The resist materials show good PED (post exposure delay) stability, high resolution, and good focus latitude and are useful for far-UV lithog.

L10 ANSWER 14 OF 14 CAPLUS COPYRIGHT 2005 ACS on STN
AN 2001:133716 CAPLUS
DN 134:200517
TI Novel onium salts as photoacid generators for resist compositions and patterning process
IN **Ohsawa, Youichi**; Watanabe, Jun; Kusaki, Wataru; Watanabe, Satoshi; Nagata, Takeshi; Nagura, Shigehiro
PA Shin-Etsu Chemical Co., Ltd., Japan
SO Eur. Pat. Appl., 77 pp.
CODEN: EPXXDW
DT Patent
LA English
FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	EP 1077391	A1	20010221	EP 2000-306997	20000816
	R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT, IE, SI, LT, LV, FI, RO				
	JP 2001122850	A2	20010508	JP 2000-245564	20000814
	US 6440634	B1	20020827	US 2000-637363	20000815
	TW 536549	B	20030611	TW 2000-89116464	20000815
PRAI	JP 1999-230122	A	19990816		
	JP 1999-230126	A	19990816		

OS MARPAT 134:200517
GI



I

AB Disclosed is a chemical amplification type resist composition that comprises as a photoacid generator novel onium salts of the formula I (R1 = C1-10 alkyl, C6-14 aryl; R2 = H, C1-6 alkyl; p = 1-5, q = 0-4, p+q = 5; R3 = C1-10 alkyl, C6-14 aryl; M = S, I; a = 3 when M=S, 2 when M=I). The chemical amplification type resist comprising the onium salt as a photoacid generator is suited for microfabrication, especially by deep UV lithog. and has many advantages including improved resolution, minimized line width variation or shape degradation even on long-term post-exposure delay, minimized defect after coating, development and stripping, and improved pattern profile after development.

RE.CNT 2 THERE ARE 2 CITED REFERENCES AVAILABLE FOR THIS RECORD
ALL CITATIONS AVAILABLE IN THE RE FORMAT

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=> d his full

     (FILE 'HOME' ENTERED AT 13:22:05 ON 14 NOV 2005)

     FILE 'REGISTRY' ENTERED AT 13:22:13 ON 14 NOV 2005
L1                STRUCTURE UPLOADED
                  D
L2              1 SEA SSS SAM L1
                  D SCAN
L3              5 SEA SSS FUL L1

     FILE 'CAPLUS' ENTERED AT 13:23:07 ON 14 NOV 2005
L4              1 SEA ABB=ON  PLU=ON  L3
                  D QUE L4 STAT
                  D IBIB IABS HITSTR
                  E OHSAWA YOUICHI/AU
L5             19 SEA ABB=ON  PLU=ON  "OHSAWA YOUICHI"/AU
                  E KOBAYASHI KATSUHIRO/AU
L6             55 SEA ABB=ON  PLU=ON  "KOBAYASHI KATSUHIRO"/AU
                  E YANAGI YOSHITAKA/AU
L7              8 SEA ABB=ON  PLU=ON  "YANAGI YOSHITAKA"/AU
                  E MAEDA KAZUNORI/AU
L8             52 SEA ABB=ON  PLU=ON  "MAEDA KAZUNORI"/AU
L9            118 SEA ABB=ON  PLU=ON  L5 OR L6 OR L7 OR L8
L10            14 SEA ABB=ON  PLU=ON  L9 AND (?DIAZOMETHANE OR DIAZOMETHANE)
                  D QUE L10 STAT
                  D 1-14 BIB ABS


     FILE HOME

     FILE REGISTRY
     Property values tagged with IC are from the ZIC/VINITI data file
     provided by InfoChem.

     STRUCTURE FILE UPDATES:   13 NOV 2005  HIGHEST RN 867336-65-0
     DICTIONARY FILE UPDATES:  13 NOV 2005  HIGHEST RN 867336-65-0

     New CAS Information Use Policies, enter HELP USAGETERMS for details.

     TSCA INFORMATION NOW CURRENT THROUGH JULY 14, 2005

       Please note that search-term pricing does apply when
       conducting SmartSELECT searches.

     ************************************************************
     *                                                          *
     * The CA roles and document type information have been removed from *
     * the IDE default display format and the ED field has been added,   *
     * effective March 20, 2005.  A new display format, IDERL, is now    *
     * available and contains the CA role and document type information. *
     *                                                          *
     ************************************************************

     Structure search iteration limits have been increased.  See HELP SLIMITS
     for details.

     REGISTRY includes numerically searchable data for experimental and
     predicted properties as well as tags indicating availability of
     experimental property data in the original document.  For information
     on property searching in REGISTRY, refer to:

     http://www.cas.org/ONLINE/UG/regprops.html
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FILE CAPLUS

FILE COVERS 1907 - 14 Nov 2005 VOL 143 ISS 21
FILE LAST UPDATED: 13 Nov 2005 (20051113/ED)

Effective October 17, 2005, revised CAS Information Use Policies apply. They are available for your review at:

http://www.cas.org/infopolicy.html

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